

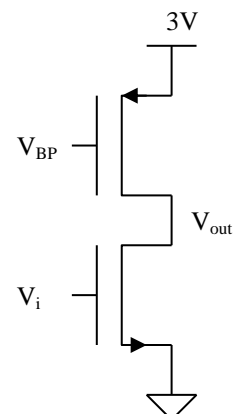
**Homework Assignment #3v2**

Due by online submission **Wednesday 2/10/2016** (Thursday 9am)

- An NPN common emitter amplifier has a 10V supply and a  $10k\Omega$  load in parallel with 100pF. Assume  $V_A=100V$ . You should be able to do all of the calculations by hand (without calculators). One-ish significant digits is fine.
  - Write an expression for  $I_C$  as a function of output bias point.
  - Write an expression for  $g_m$  and  $r_o$  as a function of output bias point.
  - Write an expression for  $A_{v0}$  as a function of output bias point.
  - For each of the output bias points {9V, 8V, 5V, 1V}, calculate the current in the device,  $g_m$ ,  $r_o$ ,  $A_{v0}$ ,  $\omega_p$ , and  $\omega_u$ . Fill in a table with those columns.
  - roughly how much does the input bias point  $V_{in}$  change over this range of output bias points?
  - Plot the output response to a 1mV input step on 3 time scales: 1ns, 1 $\mu$ s, 1ms.
- Write down a table of settling error vs. time for  $t/\tau=\{1,3,5,7\}$ . Use a calculator for this one. Memorize the table to one significant digit.
- A common source amplifier has a resistive load  $R_L$  and  $\lambda=1/(10V)$ .  $V_{DD}=2V$ , and the output bias point is 1V.
  - At this bias point, if the resistive load has the same impedance as the output resistance of the transistor, what is the supply voltage  $V_{DD}$ ?
  - Should we approximate the output resistance  $R_O$  as  $R_L$  or  $r_o$ ? Why? What error in output resistance do we get if we make that approximation?
  - With that approximation, write an expression for the gain that involves only voltages and a constant (no resistances, transconductances, etc.)
- A single-pole amplifier has a low frequency gain of 100. At 100MHz the gain is 5. What are the pole frequency and the unity gain frequency?
- Fill in the following table

$A_{v0}$	$\omega_p$	$\omega_u$		$g_m$	$r_o$	$C_L$
1000	1M					1p
	10M	1G			100k	
		1G			1M	10f
	10	1M				10p

- For the common source amplifier, assume  $\mu C_{ox}(W/L)=1mA/V^2$ ,  $|V_t|=1V$ , and  $\lambda=0.1V^{-1}$  for both devices.
  - Assuming  $V_{BP} = 1.8V$ , calculate  $V_{dsatp}$  and  $I_{dp}$  at  $V_{dp}=V_{DD}-|V_{dsatp}|$  for the PMOS transistor.
  - Plot  $|I_{dp}|$  vs.  $V_{out}$ . What is the minimum and maximum value for  $I_{dp}$  with the PMOS device in saturation in this circuit?
  - What is the approximate value of  $V_i$  for which the PMOS device is just on the edge between the saturation and linear regions? (you calculated the current and output voltage at which this happens in part A above). Considering just the current/voltage relationship for the NMOS device, plot  $I_{dn}$  at this  $V_i$  on the same plot as step B.
  - What is the value of  $V_i$  for which the NMOS device leaves saturation? Again, considering only the NMOS device, plot  $I_{dn}$  at this value of  $V_i$  on the same plot as B.
  - Based on these values, plot  $V_{out}$  vs  $V_i$ , paying careful attention to the location of the endpoints of the high gain region (calculated in parts C and D above).



- F) Based on the ( $V_i$ ,  $V_{out}$ ) pairs that you calculated in C & D, what is the gain of the amplifier? What are the input and output range over which this gain is achieved.
- G) Calculate the gain for this amplifier using the small signal model evaluated at 3 different operating points for  $V_{out}$ : the edges of the high gain region, and the center of the high gain region.